

Supporting Information

Computational Discovery of Stable Na-ion Sulfide Solid Electrolytes with High Conductivity at Room Temperature

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Discussion S1 Details of sampling protocol

Sampling space. The space group for each Ω is as follows: Na_5AlS_4 (with the orthorhombic $Pbca$ symmetry),^{1, 2} Na_5InS_4 (monoclinic $P2_1/m$),³ $Na_{4.5}Al_{0.5}Si_{0.5}S_4$ (monoclinic Cc),¹ Na_4SiS_4 (orthorhombic $P2_12_12_1$),^{1, 4-6} Na_4SnS_4 (tetragonal $P\bar{4}2_1c$),⁷⁻⁹ Na_3VS_4 (tetragonal $P\bar{4}2_1c$),¹⁰⁻¹² and Na_3SbS_4 (tetragonal $P\bar{4}2_1c$).^{1, 13-15}

Ewald summation sampling. 112 cases of (M, M', Ω) at $m = m' = 0.5$ were taken in total: 105 cases of $Na_4M_{0.5}M'_{0.5}S_4$ for $v(M) = 3$ and $v(M') = 5$ and 7 cases of $Na_{3.5}Si_{0.5}Ta_{0.5}S_4$. We conducted supercell operations on the abovementioned parent structures. We modified the number of Na-ions when necessary, and replaced host metal ion sites with M and M' . This resulted in supercells with varying numbers of ion sites: 144 for $\Omega = Na_5AlS_4$, Na_5InS_4 , $Na_{4.5}Al_{0.5}Si_{0.5}S_4$, Na_3VS_4 , and Na_3SbS_4 and 216 for $\Omega = Na_4SiS_4$ and Na_4SnS_4 with $v(M) = 3$ and $v(M') = 5$; 136 for $\Omega = Na_5AlS_4$, Na_5InS_4 , $Na_{4.5}Al_{0.5}Si_{0.5}S_4$, Na_4SnS_4 , Na_3VS_4 , and Na_3SbS_4 and 204 for Na_4SiS_4 with $Na_{3.5}Si_{0.5}Ta_{0.5}S_4$.

For each Ω with $v(M) = 3$ and $v(M') = 5$ (or with $Na_{3.5}Si_{0.5}Ta_{0.5}S_4$), a substantial number of random site arrangements was generated, ranging from 18,200 to 623,551,500 (from 33,124,000 to 2,460,781,960) and giving a total dataset size of $n_{data} = 5,290,074,920$. From these site arrangements, we selected less than 6 site arrangements with lowest Ewald Coulombic energies E_{Ewald} for each case of $Na_4M_{0.5}M'_{0.5}S_4$ or $Na_{3.5}Si_{0.5}Ta_{0.5}S_4$ ($n_{data} = 469$).¹⁶⁻¹⁸ In the subsequent step of DFT geometry optimizations, we fully relaxed the site positions and lattice parameters for the selected site arrangements. The cell structure with the lowest DFT energy E_{DFT} or, equivalently, the lowest E_{hull} , was chosen as the representative sample for each case of $Na_4M_{0.5}M'_{0.5}S_4$ or $Na_{3.5}Si_{0.5}Ta_{0.5}S_4$ for the succeeding DFT-MD sampling ($n_{data} = 16$).

Geometry optimization with DFT. This step was performed by using the Vienna Ab Initio Simulation Package (VASP). We employed the generalized gradient approximation (GGA) and the projector augmented wave (PAW) method basis set.¹⁹⁻²³ The geometry optimizations included both site positions and lattice constants. Monkhorst-Pack k -grids were set at $2 \times 2 \times 2$,²⁴ and the kinetic energy cutoff of 520 eV was used. Convergence criteria of < 0.01 eV·Å⁻¹ for forces and $< 10^{-5}$ eV·atom⁻¹ for energy were applied. Some pseudopotentials included semicore electrons as valence states for specific elements: Ca, Sc, and Zr (semicore s electrons); Na, V, Nb, and Ta (p); and Ga, In, and Sn (d). For the other elements, standard pseudopotential forms were employed. Then, the lowest-energy structure sample for each investigated composition was selected for subsequent DFT-MD calculations, wherein we calculated E_{hull} for all the samples by using the Computational Phase Diagram App provided by MaterialsProject.org^{25, 26} to verify their thermodynamic (meta)stability. Bandgap energies E_g were also examined for some of the samples by using Heyd-Scuseria-Ernzerhof hybrid functionals (HSE06) provided under VASP.²⁷

DFT-MD for the single-temperature “long-time” diagnosis. The single-temperature “long-time” diagnosis was carried out at $T = 300$ K given the geometry-optimized cell structures described above. First, a total of 10,000 DFT-MD steps (10 ps) were performed to ensure thermal equilibrations by using the Nosé-Hoover thermostat (NVT ensemble) implemented in VASP.^{28, 29} Subsequently, DFT-MD production runs were executed for trajectory sampling over $\tau = 250$ ps (NVT). Throughout the DFT-MD calculations, $\Delta\tau = 1$ fs, a $1 \times 1 \times 1$ k -grid (that is, Γ only), and a kinetic energy cutoff of 400 eV were employed. The pseudopotentials were used in their standard forms except for Nb (with semicore p electrons), and the calculations were performed using the GGA and the PAW method basis set.¹⁹⁻²³

From the sampled trajectories, the Na-ion self-diffusion coefficients $D_{Na,T} = M_s/(2d)$ at T were estimated by conducting regression analyses on the mean squared displacement (MSD) curves against sampled time intervals $\Delta\tau_{MSD}$; $D_{Na,T}$ was obtained as the slope M_s of the MSD- $\Delta\tau_{MSD}$ regression line at T , considering the three-dimensional nature of Na-ion diffusion ($d = 3$). Then, the Na-ion ionic conductivity $\sigma_{Na,T}$ at T is estimated by using the Nernst-Einstein equation

$$\sigma_{Na,T} = \frac{(z_{Na}F)^2 \rho_{Na}}{RT} D_{Na,T}, \quad (S1)$$

where z_{Na} ($=+1$) is the valence for a Na-ion, ρ_{Na} is the Na-ion density, and F and R denote the Faraday constant and the gas constant, respectively.

DFT-MD for multi-temperature calculations. The multi-temperature DFT-MD calculations were conducted at $T = 500, 600, 700, 800,$ and 900 K for Na_4SiS_4 , $Na_4Ga_{0.125}Si_{0.75}P_{0.125}S_4$, $Na_4Ga_{0.25}Si_{0.5}P_{0.25}S_4$, $Na_4Ga_{0.375}Si_{0.25}P_{0.375}S_4$, $Na_4Ga_{0.5}P_{0.5}S_4$, $Na_{3.75}Ga_{0.375}P_{0.625}S_4$, $Na_{4.25}Ga_{0.625}P_{0.375}S_4$, $Na_{3.875}Si_{0.875}Ta_{0.125}S_4$, $Na_{3.75}Si_{0.75}Ta_{0.25}S_4$, $Na_{3.625}Si_{0.625}Ta_{0.375}S_4$, and $Na_{3.5}Si_{0.5}Ta_{0.5}S_4$ with $\Omega = Na_4SiS_4$. First, a total of 40,000 DFT-MD steps (40 ps) were performed to achieve thermal and volume equilibrations by using the Langevin thermostat with the Parinello-Rahman algorithm (NpT ensemble) implemented in VASP.^{30, 31} During this process, the averaged lattice constants were calculated over the last 10,000 DFT-MD steps (30 - 40 ps) to account cell volumes expanded thermally. Subsequently, with the averaged lattice constants, thermal equilibration runs were repeated for 10,000 DFT-MD steps (10 ps) under the Nosé-Hoover thermostat (NVT). Finally, product runs were conducted afterwards for trajectory sampling over $\tau = 100$ ps (NVT). Meanwhile, the choices of $\Delta\tau$, the k -grid, the kinetic energy cutoff,

and the pseudopotentials and the post-process for $D_{Na,T}$ and $\sigma_{Na,T}$ were common to those of the DFT-MD for the single-temperature “long-time” diagnosis

Na ₄ Ga _{0.5} Sb _{0.5} S ₄	Na ₆₄ Ga ₈ Sb ₈ S ₆₄	Na ₃ SbS ₄	20.325	13.580	20.759	90.656	89.115	90.377	5728.5	44.2
Na ₄ Ga _{0.5} Ta _{0.5} S ₄	Na ₆₄ Ga ₈ Ta ₈ S ₆₄	Na ₅ AlS ₄	12.176	14.211	21.575	91.189	89.572	89.006	3731.9	35.9
Na ₄ Ga _{0.5} Ta _{0.5} S ₄	Na ₆₄ Ga ₈ Ta ₈ S ₆₄	Na ₃ InS ₄	13.968	17.881	14.766	88.324	87.413	89.145	3682.3	27.7
Na ₄ Ga _{0.5} Ta _{0.5} S ₄	Na ₉₆ Ga ₁₂ Ta ₁₂ S ₉₆	Na _{4.5} Al _{0.5} Si _{0.5} S ₄	17.942	13.951	14.539	89.594	93.122	89.533	3633.7	22.1
Na ₄ Ga _{0.5} Ta _{0.5} S ₄	Na ₉₆ Ga ₁₂ Ta ₁₂ S ₉₆	Na ₄ SiS ₄	42.303	8.9968	14.106	90.028	90.293	90.068	5368.5	19.7
Na ₄ Ga _{0.5} Ta _{0.5} S ₄	Na ₆₄ Ga ₈ Ta ₈ S ₆₄	Na ₄ SnS ₄	15.698	15.698	13.896	90.000	90.000	90.000	3424.6	20.6
Na ₄ Ga _{0.5} Ta _{0.5} S ₄	Na ₆₄ Ga ₈ Ta ₈ S ₆₄	Na ₃ VS ₄	14.759	14.822	16.418	89.175	87.358	89.305	3587.1	56.3
Na ₄ Ga _{0.5} Ta _{0.5} S ₄	Na ₆₄ Ga ₈ Ta ₈ S ₆₄	Na ₃ SbS ₄	19.927	13.099	21.395	91.280	90.020	90.630	5582.6	44.5
Na ₄ In _{0.5} P _{0.5} S ₄	Na ₆₄ In ₈ P ₈ S ₆₄	Na ₅ AlS ₄	11.758	14.352	21.597	92.324	90.350	89.461	3641.1	51.8
Na ₄ In _{0.5} P _{0.5} S ₄	Na ₆₄ In ₈ P ₈ S ₆₄	Na ₃ InS ₄	13.861	18.128	14.778	89.377	86.092	89.224	3704.0	33.7
Na ₄ In _{0.5} P _{0.5} S ₄	Na ₆₄ In ₈ P ₈ S ₆₄	Na _{4.5} Al _{0.5} Si _{0.5} S ₄	17.824	14.209	14.613	90.834	94.312	90.583	3689.9	42.7
Na ₄ In _{0.5} P _{0.5} S ₄	Na ₉₆ In ₁₂ P ₁₂ S ₉₆	Na ₄ SiS ₄	42.123	9.1717	13.892	89.908	90.168	90.030	5366.9	31.1
Na ₄ In _{0.5} P _{0.5} S ₄	Na ₉₆ In ₁₂ P ₁₂ S ₉₆	Na ₄ SnS ₄	15.933	15.933	13.645	90.000	90.000	90.000	3463.9	30.8
Na ₄ In _{0.5} P _{0.5} S ₄	Na ₆₄ In ₈ P ₈ S ₆₄	Na ₃ VS ₄	14.500	15.823	15.860	88.948	92.706	88.796	3633.4	55.1
Na ₄ In _{0.5} P _{0.5} S ₄	Na ₆₄ In ₈ P ₈ S ₆₄	Na ₃ SbS ₄	20.314	13.460	20.538	90.131	90.212	89.445	5615.3	59.8
Na ₄ In _{0.5} V _{0.5} S ₄	Na ₆₄ In ₈ V ₈ S ₆₄	Na ₅ AlS ₄	11.772	14.432	21.640	91.785	89.711	89.663	3674.7	55.4
Na ₄ In _{0.5} V _{0.5} S ₄	Na ₆₄ In ₈ V ₈ S ₆₄	Na ₃ InS ₄	13.691	17.872	15.051	89.244	87.699	89.753	3679.4	44.4
Na ₄ In _{0.5} V _{0.5} S ₄	Na ₆₄ In ₈ V ₈ S ₆₄	Na _{4.5} Al _{0.5} Si _{0.5} S ₄	17.978	13.904	14.606	89.676	93.832	89.813	3642.7	44.8
Na ₄ In _{0.5} V _{0.5} S ₄	Na ₉₆ In ₁₂ V ₁₂ S ₉₆	Na ₄ SiS ₄	42.274	9.0120	14.086	89.936	90.260	90.002	5366.3	37.1
Na ₄ In _{0.5} V _{0.5} S ₄	Na ₉₆ In ₁₂ V ₁₂ S ₉₆	Na ₄ SnS ₄	15.830	15.830	13.822	90.000	90.000	90.000	3463.7	35.9
Na ₄ In _{0.5} V _{0.5} S ₄	Na ₆₄ In ₈ V ₈ S ₆₄	Na ₃ VS ₄	15.310	14.424	16.386	87.890	90.168	87.426	3612.3	68.6
Na ₄ In _{0.5} V _{0.5} S ₄	Na ₆₄ In ₈ V ₈ S ₆₄	Na ₃ SbS ₄	20.277	13.405	21.038	90.621	89.971	89.915	5718.0	70.3
Na ₄ In _{0.5} Nb _{0.5} S ₄	Na ₆₄ In ₈ Nb ₈ S ₆₄	Na ₅ AlS ₄	12.341	14.497	21.644	91.067	89.627	89.418	3871.3	53.8
Na ₄ In _{0.5} Nb _{0.5} S ₄	Na ₆₄ In ₈ Nb ₈ S ₆₄	Na ₃ InS ₄	13.734	17.925	15.315	89.199	88.186	89.796	3767.8	34.8
Na ₄ In _{0.5} Nb _{0.5} S ₄	Na ₆₄ In ₈ Nb ₈ S ₆₄	Na _{4.5} Al _{0.5} Si _{0.5} S ₄	18.133	14.160	14.717	89.714	93.364	89.577	3772.0	37.3
Na ₄ In _{0.5} Nb _{0.5} S ₄	Na ₉₆ In ₁₂ Nb ₁₂ S ₉₆	Na ₄ SnS ₄	15.836	15.836	13.969	90.000	90.000	90.000	3503.3	23.5
Na ₄ In _{0.5} Nb _{0.5} S ₄	Na ₆₄ In ₈ Nb ₈ S ₆₄	Na ₃ VS ₄	14.799	14.470	17.068	89.110	88.201	88.816	3651.8	64.4
Na ₄ In _{0.5} Nb _{0.5} S ₄	Na ₆₄ In ₈ Nb ₈ S ₆₄	Na ₃ SbS ₄	20.598	13.690	20.627	89.555	90.625	90.787	5815.5	58.1
Na ₄ In _{0.5} Sb _{0.5} S ₄	Na ₆₄ In ₈ Sb ₈ S ₆₄	Na ₅ AlS ₄	12.390	14.411	21.110	90.680	89.885	89.314	3768.8	48.7
Na ₄ In _{0.5} Sb _{0.5} S ₄	Na ₆₄ In ₈ Sb ₈ S ₆₄	Na ₃ InS ₄	13.744	18.116	15.357	89.189	87.797	89.721	3820.6	37.5
Na ₄ In _{0.5} Sb _{0.5} S ₄	Na ₉₆ In ₁₂ Sb ₁₂ S ₉₆	Na _{4.5} Al _{0.5} Si _{0.5} S ₄	18.257	14.280	14.711	89.514	92.722	89.247	3830.7	44.1
Na ₄ In _{0.5} Sb _{0.5} S ₄	Na ₉₆ In ₁₂ Sb ₁₂ S ₉₆	Na ₄ SiS ₄	42.153	9.4950	14.132	89.886	90.249	90.065	5656.0	36.6
Na ₄ In _{0.5} Sb _{0.5} S ₄	Na ₆₄ In ₈ Sb ₈ S ₆₄	Na ₄ SnS ₄	15.916	15.916	13.957	90.000	90.000	90.000	3535.6	17.4
Na ₄ In _{0.5} Sb _{0.5} S ₄	Na ₆₄ In ₈ Sb ₈ S ₆₄	Na ₃ VS ₄	14.857	15.198	16.623	89.589	87.892	89.608	3750.7	56.7
Na ₄ In _{0.5} Sb _{0.5} S ₄	Na ₆₄ In ₈ Sb ₈ S ₆₄	Na ₃ SbS ₄	20.936	13.919	20.249	90.720	88.452	89.507	5897.6	60.0
Na ₄ In _{0.5} Ta _{0.5} S ₄	Na ₆₄ In ₈ Ta ₈ S ₆₄	Na ₅ AlS ₄	12.350	14.500	21.647	91.009	89.503	89.417	3875.4	56.3
Na ₄ In _{0.5} Ta _{0.5} S ₄	Na ₆₄ In ₈ Ta ₈ S ₆₄	Na ₃ InS ₄	13.765	17.962	15.279	89.131	87.971	89.767	3775.0	36.8
Na ₄ In _{0.5} Ta _{0.5} S ₄	Na ₉₆ In ₁₂ Ta ₁₂ S ₉₆	Na _{4.5} Al _{0.5} Si _{0.5} S ₄	18.136	14.143	14.729	89.680	93.319	89.586	3771.5	39.9
Na ₄ In _{0.5} Ta _{0.5} S ₄	Na ₉₆ In ₁₂ Ta ₁₂ S ₉₆	Na ₄ SiS ₄	42.515	9.2180	14.184	89.963	90.513	90.026	5558.5	38.8
Na ₄ In _{0.5} Ta _{0.5} S ₄	Na ₆₄ In ₈ Ta ₈ S ₆₄	Na ₄ SnS ₄	15.845	15.845	13.970	90.000	90.000	90.000	3507.2	26.0
Na ₄ In _{0.5} Ta _{0.5} S ₄	Na ₆₄ In ₈ Ta ₈ S ₆₄	Na ₃ VS ₄	14.899	14.593	16.949	89.268	88.186	88.355	3681.4	62.3
Na ₄ In _{0.5} Ta _{0.5} S ₄	Na ₆₄ In ₈ Ta ₈ S ₆₄	Na ₃ SbS ₄	21.081	13.973	20.244	89.628	87.973	89.403	5959.4	75.4
Na _{3.5} Si _{0.5} Ta _{0.5} S ₄	Na ₅₆ Si ₈ Ta ₈ S ₆₄	Na ₅ AlS ₄	11.602	14.197	22.060	90.395	91.871	90.771	3631.3	44.7
Na _{3.5} Si _{0.5} Ta _{0.5} S ₄	Na ₅₆ Si ₈ Ta ₈ S ₆₄	Na ₃ InS ₄	13.625	18.213	14.391	90.715	86.832	91.114	3565.0	30.6
Na _{3.5} Si _{0.5} Ta _{0.5} S ₄	Na ₅₆ Si ₈ Ta ₈ S ₆₄	Na _{4.5} Al _{0.5} Si _{0.5} S ₄	17.824	13.896	14.345	91.525	93.518	90.139	3545.0	31.7
Na _{3.5} Si _{0.5} Ta _{0.5} S ₄	Na ₈₄ Si ₁₂ Ta ₁₂ S ₉₆	Na ₄ SiS ₄	41.654	8.9369	14.080	90.072	89.220	90.088	5241.0	24.1
Na _{3.5} Si _{0.5} Ta _{0.5} S ₄	Na ₅₆ Si ₈ Ta ₈ S ₆₄	Na ₄ SnS ₄	15.802	15.445	13.845	90.360	90.620	89.424	3378.6	24.3
Na _{3.5} Si _{0.5} Ta _{0.5} S ₄	Na ₅₆ Si ₈ Ta ₈ S ₆₄	Na ₃ VS ₄	14.192	13.926	16.324	89.917	89.817	89.664	3226.1	42.6

Table S2 Na-ion conductivity $\sigma_{Na,T}$ (in S·cm⁻¹) and Na-ion self-diffusion coefficient $D_{Na,T}$ (in cm²·s⁻¹) for the 11 compositions adopted in the multi-temperature diagnosis with $\Delta\tau = 1$ fs, $\tau = 100$ ps, and $T = 500, 600, 700, 800,$ and 800 K (“-” denotes the absence of observed Na-ion migrations). By extrapolating the values in the Arrhenius plots [see Figures 1(i) and 2(h)], Na-ion activation energies E_a and $\sigma_{Na,300K}$ were estimated as well. In E_a , the standard errors are presented. In the first row, the compositions per unit cell are presented in parentheses.

Composition	$\sigma_{Na,300K}$ ($D_{Na,300K}$)	$\sigma_{Na,500K}$ ($D_{Na,500K}$)	$\sigma_{Na,600K}$ ($D_{Na,600K}$)	$\sigma_{Na,700K}$ ($D_{Na,700K}$)	$\sigma_{Na,800K}$ ($D_{Na,800K}$)	$\sigma_{Na,900K}$ ($D_{Na,900K}$)	E_a (meV)
Na_4SiS_4 ($Na_{96}Si_{24}S_{96}$)	2.57×10^{-15} (2.00×10^{-20})	-	7.01×10^{-5} (1.26×10^{-9})	3.48×10^{-4} (7.43×10^{-9})	1.38×10^{-2} (3.40×10^{-7})	1.16×10^{-1} (3.27×10^{-6})	1250 ± 145
$Na_4Ga_{0.125}Si_{0.75}P_{0.125}S_4$ ($Na_{96}Ga_3Si_{18}P_3S_{96}$)	2.26×10^{-11} (1.84×10^{-16})	4.47×10^{-5} (6.69×10^{-10})	-	1.14×10^{-2} (2.45×10^{-7})	1.98×10^{-1} (4.99×10^{-6})	4.11×10^{-1} (1.18×10^{-5})	965 ± 43.1
$Na_4Ga_{0.25}Si_{0.5}P_{0.25}S_4$ ($Na_{96}Ga_6Si_{12}P_6S_{96}$)	9.48×10^{-9} (7.89×10^{-14})	5.11×10^{-4} (7.73×10^{-9})	7.39×10^{-3} (1.35×10^{-7})	1.66×10^{-1} (3.63×10^{-6})	1.25×10^{-1} (3.15×10^{-6})	7.13×10^{-1} (2.05×10^{-5})	747 ± 88.1
$Na_4Ga_{0.375}Si_{0.25}P_{0.375}S_4$ ($Na_{96}Ga_9Si_6P_9S_{96}$)	6.03×10^{-11} (4.89×10^{-16})	4.52×10^{-5} (6.83×10^{-10})	1.04×10^{-2} (1.92×10^{-7})	1.88×10^{-2} (4.07×10^{-7})	2.12×10^{-1} (5.39×10^{-6})	7.08×10^{-1} (2.07×10^{-5})	948 ± 111
$Na_4Ga_{0.5}P_{0.5}S_4$ ($Na_{96}Ga_{12}P_{12}S_{96}$)	9.71×10^{-4} (7.92×10^{-9})	7.00×10^{-2} (1.07×10^{-6})	1.51×10^{-1} (2.78×10^{-6})	1.48×10^{-1} (3.28×10^{-6})	6.39×10^{-1} (1.65×10^{-5})	8.24×10^{-1} (2.41×10^{-5})	297 ± 56.3
$Na_{3.75}Ga_{0.375}P_{0.625}S_4$ ($Na_{90}Ga_9P_{15}S_{96}$)	2.07×10^{-3} (1.77×10^{-8})	1.19×10^{-1} (1.91×10^{-6})	2.77×10^{-1} (5.41×10^{-6})	4.35×10^{-1} (1.02×10^{-5})	9.44×10^{-1} (2.55×10^{-5})	1.30×10^0 (4.07×10^{-5})	290 ± 18.0
$Na_{4.25}Ga_{0.625}P_{0.375}S_4$ ($Na_{102}Ga_{15}P_9S_{96}$)	6.57×10^{-4} (5.26×10^{-9})	4.96×10^{-2} (7.23×10^{-7})	1.83×10^{-1} (3.27×10^{-6})	2.61×10^{-1} (5.47×10^{-6})	4.52×10^{-1} (1.10×10^{-5})	8.61×10^{-1} (2.41×10^{-5})	316 ± 22.6
$Na_{3.875}Si_{0.875}Ta_{0.125}S_4$ ($Na_{93}Si_{21}Ta_3S_{96}$)	4.93×10^{-5} (4.22×10^{-10})	2.06×10^{-2} (3.19×10^{-7})	6.53×10^{-2} (1.24×10^{-6})	1.47×10^{-1} (3.30×10^{-6})	4.06×10^{-1} (1.05×10^{-5})	8.40×10^{-1} (2.48×10^{-5})	413 ± 27.4
$Na_{3.75}Si_{0.75}Ta_{0.25}S_4$ ($Na_{90}Si_{18}Ta_6S_{96}$)	2.36×10^{-3} (2.10×10^{-8})	8.62×10^{-2} (1.39×10^{-6})	1.38×10^{-1} (2.72×10^{-6})	9.09×10^{-2} (2.11×10^{-6})	4.26×10^{-1} (1.14×10^{-5})	6.83×10^{-1} (2.09×10^{-5})	246 ± 77.5
$Na_{3.625}Si_{0.625}Ta_{0.375}S_4$ ($Na_{87}Si_{15}Ta_9S_{96}$)	4.53×10^{-3} (4.25×10^{-8})	1.12×10^{-1} (1.91×10^{-6})	4.70×10^{-1} (9.75×10^{-6})	3.78×10^{-1} (9.23×10^{-6})	7.64×10^{-1} (2.14×10^{-5})	1.02×10^0 (3.32×10^{-5})	252 ± 40.8
$Na_{3.5}Si_{0.5}Ta_{0.5}S_4$ ($Na_{84}Al_{12}Ta_{12}S_{96}$)	1.35×10^{-2} (1.27×10^{-7})	2.53×10^{-1} (4.47×10^{-6})	3.90×10^{-1} (8.39×10^{-6})	5.34×10^{-1} (1.35×10^{-5})	1.03×10^0 (3.07×10^{-5})	1.23×10^0 (4.22×10^{-5})	215 ± 21.7

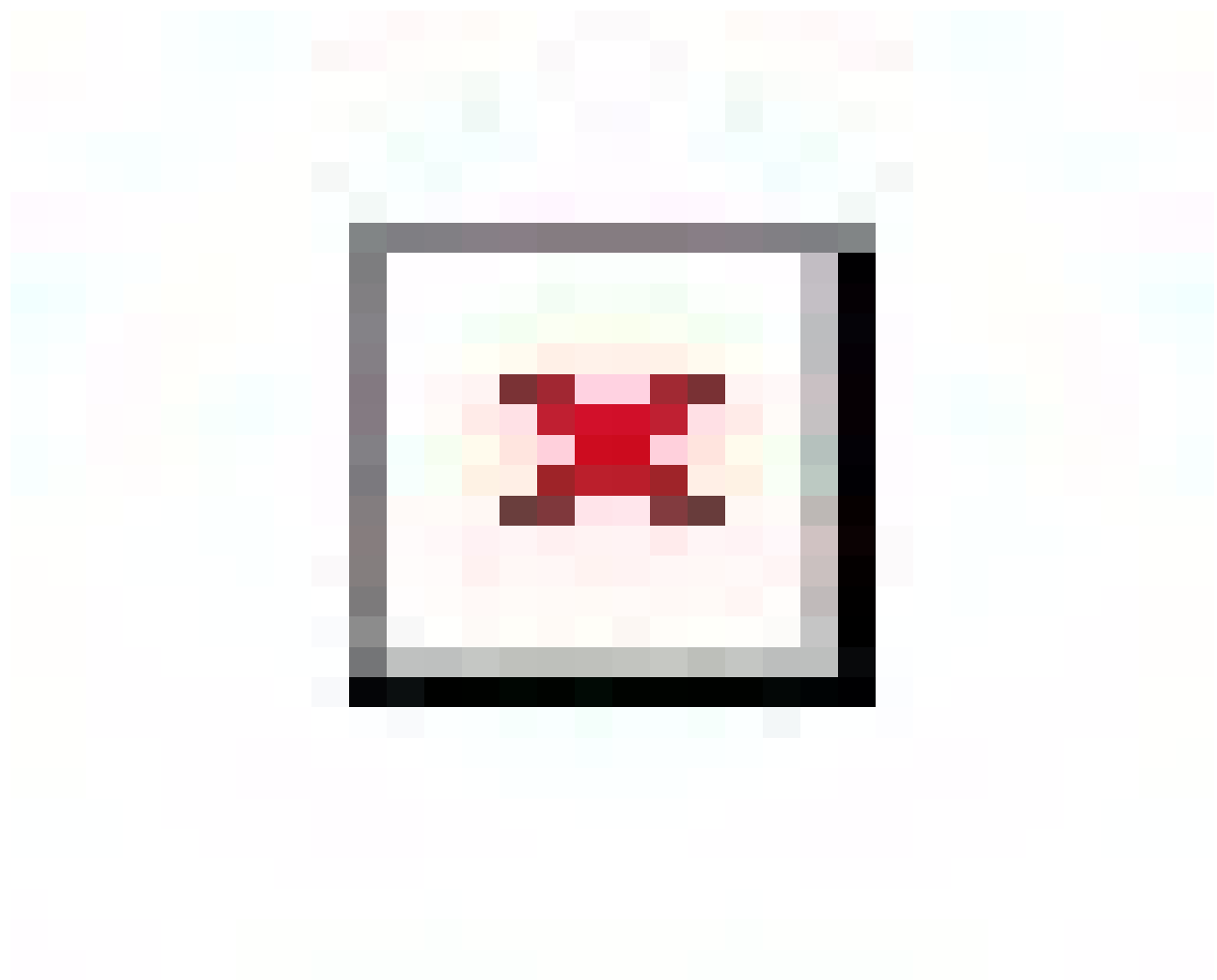


Figure S1 Mean squared displacement (MSD) curves against sampled time intervals $\Delta\tau_{MSD}$ given by the multi-temperature diagnosis (with $\Delta\tau = 1$ fs and $\tau = 100$ ps at $T = 500, 600, 700, 800,$ and 900 K) for the seven samples within $(M, M', \Omega) = (Ga, P, Na_4SiS_4)$: (a) Na_4SiS_4 , (b) $Na_4Ga_{0.125}Si_{0.75}P_{0.125}S_4$, (c) $Na_4Ga_{0.25}Si_{0.5}P_{0.25}S_4$, (d) $Na_4Ga_{0.375}Si_{0.25}P_{0.375}S_4$, (e) $Na_4Ga_{0.5}P_{0.5}S_4$, (f) $Na_{3.75}Ga_{0.375}P_{0.625}S_4$, and (g) $Na_{4.25}Ga_{0.625}P_{0.375}S_4$. The dashed lines with slopes represent regression analyses, and the insets present the trajectory density plot at $T = 500$ K represented by yellow isosurfaces.

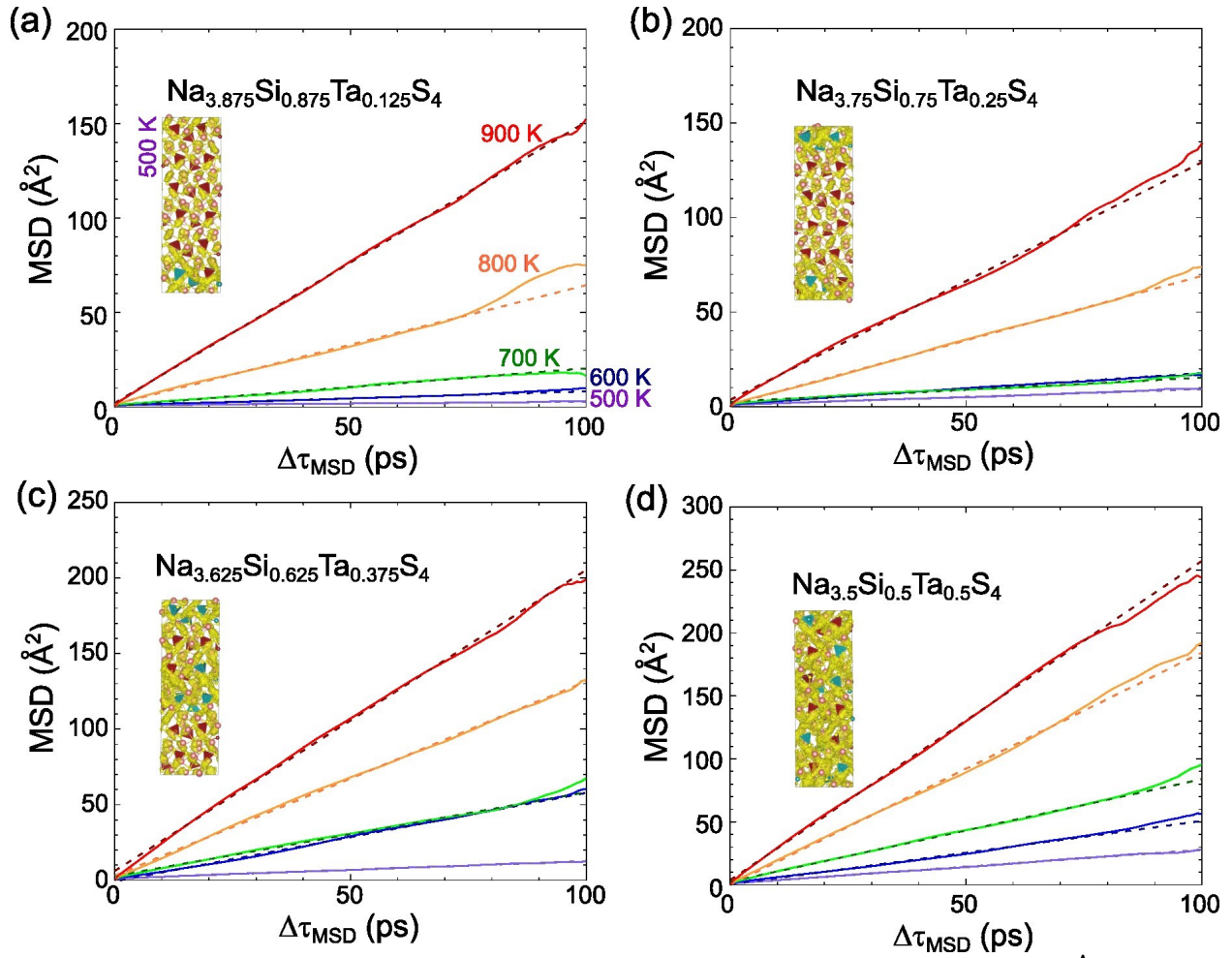


Figure S2 Mean squared displacement (MSD) curves against sampled time intervals $\Delta\tau_{MSD}$ given by the multi-temperature diagnosis (with $\Delta\tau = 1$ fs and $\tau = 100$ ps at $T = 500, 600, 700, 800,$ and 900 K) for the four samples within $(M, M', \Omega) = (Si, Ta, Na_4SiS_4)$: $Na_{3.875}Si_{0.875}Ta_{0.125}S_4$, $Na_{3.75}Si_{0.75}Ta_{0.25}S_4$, $Na_{3.625}Si_{0.625}Ta_{0.375}S_4$, and $Na_{3.5}Si_{0.5}Ta_{0.5}S_4$. For the MSD curves of Na_4SiS_4 , Figure S1a is referred to. The dashed lines with slopes represent regression analyses, and the insets present the trajectory density plot at $T = 500$ K represented by yellow isosurfaces.

Discussion S2 Electrochemical stability windows

We present the electrochemical stability windows and decomposition phases for the materials systems $(M, M', \Omega) = (Ga, P, Na_4SiS_4)$ and (Si, Ta, Na_4SiS_4) in Table S3. These values were calculated using the Computational Phase Diagram App provided by MaterialsProject.org.^{25, 26} The electrochemical stability window for $Na_4Ga_{0.125}Si_{0.75}P_{0.125}S_4$, $Na_4Ga_{0.25}Si_{0.5}P_{0.25}S_4$, $Na_4Ga_{0.375}Si_{0.25}P_{0.375}S_4$, $Na_4Ga_{0.5}P_{0.5}S_4$, $Na_{3.75}Ga_{0.375}P_{0.625}S_4$, and $Na_{4.25}Ga_{0.625}P_{0.375}S_4$ is [1.24, 1.55] V vs. Na/Na⁺, with multiple decomposition phases identified as Na_4SiS_4 , Na_3GaS_3 , Na_3PS_4 , and Na_2S . When these decomposition phases form around solid interface regions, such as at the anode and cathode, the interphase-controlled electrochemical stability windows extend to [0.77, 2.12] V vs. Na/Na⁺.

Similarly, the electrochemical stability window for $Na_{3.875}Si_{0.875}Ta_{0.125}S_4$, $Na_{3.75}Si_{0.75}Ta_{0.25}S_4$, $Na_{3.625}Si_{0.625}Ta_{0.375}S_4$, and $Na_{3.5}Si_{0.5}Ta_{0.5}S_4$ is [1.00, 1.91] V vs. Na/Na⁺, with decomposition phases being Na_4SiS_4 and Na_3TaS_4 . The interphase-controlled electrochemical stability window for these materials extends to [0.77, 2.03] V versus Na/Na⁺. Given that the narrow electrochemical stability windows for $(M, M', \Omega) = (Ga, P, Na_4SiS_4)$ and (Si, Ta, Na_4SiS_4) are not significantly improved by interphase control, it is advisable to incorporate electrochemically stable interphase layers in battery design.³² This is particularly important at the interfaces between the solid electrolyte and the anode, as well as between the solid electrolyte and the cathode.

Table S3. Electrochemical stability windows for the 11 compositions and decomposition phases adopted in the multi-temperature diagnosis.

Composition	Electrochemical stability windows (potential ϕ in V vs. Na/Na ⁺) (Corresponding decomposition phases if exist)
Na_4SiS_4	[0.77, 1.91]
$Na_4Ga_{0.125}Si_{0.75}P_{0.125}S_4$	[1.24, 1.55] ($Na_4SiS_4, Na_3GaS_3, Na_3PS_4, Na_2S$)
$Na_4Ga_{0.25}Si_{0.5}P_{0.25}S_4$	[1.24, 1.55] ($Na_4SiS_4, Na_3GaS_3, Na_3PS_4, Na_2S$)
$Na_4Ga_{0.375}Si_{0.25}P_{0.375}S_4$	[1.24, 1.55] ($Na_4SiS_4, Na_3GaS_3, Na_3PS_4, Na_2S$)
$Na_4Ga_{0.5}P_{0.5}S_4$	[1.24, 1.55] ($Na_3GaS_3, Na_3PS_4, Na_2S$)
$Na_{3.75}Ga_{0.375}P_{0.625}S_4$	[1.24, 1.55] ($Na_3GaS_3, Na_3PS_4, Na_2S$)
$Na_{4.25}Ga_{0.625}P_{0.375}S_4$	[1.24, 1.55] ($Na_3GaS_3, Na_3PS_4, Na_2S$)
$Na_{3.875}Si_{0.875}Ta_{0.125}S_4$	[1.00, 1.91] (Na_4SiS_4, Na_3TaS_4)
$Na_{3.75}Si_{0.75}Ta_{0.25}S_4$	[1.00, 1.91] (Na_4SiS_4, Na_3TaS_4)
$Na_{3.625}Si_{0.625}Ta_{0.375}S_4$	[1.00, 1.91] (Na_4SiS_4, Na_3TaS_4)
$Na_{3.5}Si_{0.5}Ta_{0.5}S_4$	[1.00, 1.91] (Na_4SiS_4, Na_3TaS_4)
Na_3GaS_3	[0.79, 1.65]
Na_3PS_4	[1.24, 2.12]
Na_2S	[0, 1.55]
Na_3TaS_4	[1.00, 2.03]

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